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Dr. Tomas Palacios

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Dr. Palacios leads the Wide-bandgap Semiconductor Materials and Devices Group at the Microsystems Technology Laboratories of the Massachusetts Institute of Technology. His research focuses on the development of new electronic devices to advance the fields of information technology, biosensors and energy conversion. He is especially interested in expanding the frequency performance transistors, heterogeneous integration of GaN and Si electronics, and new applications for graphene.

He received his PhD from the University of California – Santa Barbara in 2006, where he set the state-of-the-art in high-frequency high-power nitride transistors. Between 1998 and 2002, while in Spain, he developed ultraviolet detectors and surface acoustic wave devices for sensor and mobile telephone applications. He has also worked at the European Organization for Nuclear Research (CERN), where he contributed to the design of solid-state particle detectors.

Dr. Palacios' work has been recognized with several awards such as the 2009 ONR Young Investigator Award, the 2008 DARPA Young Faculty Award, the 2006 UCSB Lancaster Award, the Young Researcher Award at the 6th International Conference on Nitride Semiconductors, the Best Student Paper Award at the 63rd IEEE Device Research Conference, and the European Prize Salva i Campillo. His students have also received awards such as the 2008 Best Paper Award at the International Conference on Advances in Electronics and Microelectronics and the 2007 IEEE Electron Device Society Masters Student Fellowship. Tomas Palacios has authored more than 100 contributions on advanced semiconductor devices in international journals and conferences, 30 of them invited, and several book chapters and patents.

Dr. Palacios contributions also include serving on the program committee of the International Electron Device Meeting, the Device Research Conference, the International Conference on Nitride Semiconductors. Dr. Palacios is a member of the Institute of Electrical and Electronics Engineers and the American Physical Society.